Total number of printed pages-6

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### 2021

## TRANSDUCER ENGINEERING

Paper : IE 502

Full Marks : 100

Time : Three hours

# The figures in the margin indicate full marks for the questions.

### Answer any five questions.

- 1. (a) What are the materials used for RTDs? Write down the R-T relation for *Pt*-RTD and draw its R-T characteristics. 4
  - (b) A given Pt-RTD has  $100\Omega$  and  $\alpha = 0.00389 (\Omega/K)$  at 0°C. Calculate its sensitivity and temperature coefficients at 55°C and 90°C. 6
  - (c) Calculate  $\beta$  for an NTC thermistor that has  $5k\Omega$  at  $25^{\circ}C$  and  $1.24k\Omega$  at  $60^{\circ}C$ .

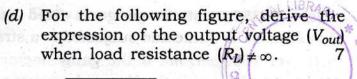
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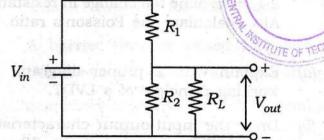
- (d) Define the following terms for photoresistive sensors — 6
  - (i) responsivety
  - (ii) noise equivalent power
  - (iii) detectivity and
  - (iv) quantum efficiency.
- 2. (a) Mention the advantages and disadvantages of a potentiometer. 4
  - (b) Explain how a potentiometer can be used to measure linear displacement.

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(c) A potentiometer used for linear displacement provides 1.25 V output voltage when linear displacement is 15 mm and 3.45 V for 85 mm. Determine the linear displacement when the output voltage is 1.95 V.

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Also, determine the value of  $V_{out}$  when  $R_1 = 10 k\Omega$ ,  $R_2 = 5 k\Omega$ ,  $R_L = 10 k\Omega$  and  $V_{in} = 10 V$ .

3. (a) Prove that  $G_f = 1 + 2\nu + \left(\frac{\Delta \rho / \rho}{\Delta l / l}\right)$ ; where

 $G_f$  is the gauge factor, v is the

Poisson's ratio and  $\left(\frac{\Delta \rho / \rho}{\Delta l / l}\right)$  is the

change in resistance due to piezoresistive effect. 8

 (b) Explain how dummy gauge can be used to compensate the effect of ambient temperature in measurement.

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- (c) A 350 Ω strain gauge is fixed as a metallic frame and subjected to a strain of 1500 µm/m. If the gauge factor is 2.1, determine the change in resistance. Also, calculate the Poisson's ratio.
- (a) Explain with a proper diagram, the working principle of a LVDT. 8
  - (b) Draw the input-output characteristics of a LVDT and explain it. What is residual voltage and how it can be eliminated?
  - (c) A capacitive sensor of two parallel plates of overlapping area of  $5 \cdot 5 \times 10^{-4} m^2$  is immersed in water. The capacitance has found to be  $8 \cdot 7 pF$ . Calculate the separation between the plates and the sensitivity of the sensor. [Given, relative permittivity of water = 81 and permittivity in free space =  $8 \cdot 854 pF/m$ ].

Define the terms: change sensitivity and voltage sensitivity of a PZT. Drive the different relationships between then. 7

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(a)

- (b) Draw the block diagram and electrical equivalent circuit of a PZT based measurement system. Derive the transfer function for the same. 8
- (c) A barrier titanate based PZT has a thickness of 4.6mm and a voltage sensitivity of  $8 \times 10^{-3} V \cdot m/N$ . Determine the output voltage when it is subjected to a pressure of  $3.5 \times 10^6 N/m^2$ . 5
- (a) What is Hall effect? Explain the working principle of Hall effect sensor.
  - (b) Explain with a proper diagram, the working principle of Eddy current sensor.
  - (c) Explain how a diode/transistor can be used to measure temperature.
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(d) What do you understand by smart sensors?

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- 7. Write short notes on : (any four) 5×4=20
  - (i) Capacitive sensor for moisture measurement.
  - (ii) RTD in Wheatstone bridge for temperature—measurement.

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- (iii) Calibration of strain gauge
- (iv) Differential inductive sensor
- (v) Law of intermediate metal in thermocouple.

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Explain how a diode/transistor can he

used to measure temperature..

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